















ESD

TVS

MOS

LDO

Diode

Sensor

DC-DC

Product Specification

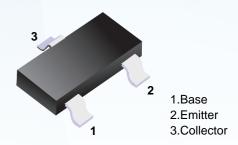
Domestic Part Number	EVBC849-EVBC850
Overseas Part Number	BC849-BC850
▶ Equivalent Part Number	BC849-BC850

"S1" means SOT-23





NPN Transistors



■ Simplified outline(SOT-23)

■ Features

Low current (max. 100 mA)

Low voltage (max. 45 V).

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
collector-base voltage	Vсво	30	V	
Collector-base voltage	V CBO	50	V	
collector emitter veltage	Vceo	30	V	
collector-emitter voltage	VCEO	45	V	
emitter-base voltage	Vево	5	V	
collector current (DC)	Ic	100	mA	
peak collector current	Ісм	200	mA	
peak base current	Івм	200	mA	
total power dissipation T _{amb} ≤25 °C *	Ptot	250	mW	
storage temperature	Tstg	-65 to 150	$^{\circ}\mathbb{C}$	
junction temperature	Tj	150	℃	
operating ambient temperature	Tamb	-65 to 150	℃	
thermal resistance from junction to ambient *	Rth(j-a)	500	K/W	

^{*} Transistor mounted on an FR4 printed-circuit board.



■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
collector cut-off current	Ісво	IE = 0; VCB = 30 V			15	nA
collector cut-on current	ICBO	IE = 0; VcB = 30 V; Tj = 150 □C			5	μA
emitter cut-off current	ІЕВО	IC = 0; VEB = 5 V			100	nA
DC current gain EVBC849B; EVBC850B		In = 40 A. Von = 5 Vo		240		
EVBC849C; EVBC850C	I	Ic = 10 μA; Vcε = 5 V;		450		
DC current gain EVBC849B; EVBC850B	hfE	Ic = 2 mA; VcE = 5 V;	200	290	450	
EVBC849C; EVBC850C		IC - 2 IIIA, VCE - 5 V,	420	520	800	
collector-emitter saturation voltage	VCEsat	Ic = 10 mA; Iв = 0.5 mA		90	250	mV
collector-entitler saturation voltage	V CESat	Ic = 100 mA; IB = 5 mA		200	600	mV
base-emitter saturation voltage	VBEsat	Ic = 10 mA; Iв = 0.5 mA; *1		700		mV
base-enfiller saturation voltage	V DESAL	Ic = 100 mA; Iв = 5 mA; *1		900		mV
base-emitter voltage	VBE	Ic = 2 mA; VcE = 5 V; *2	580	660	700	mV
base-enfiller voltage	VBE	Ic = 10 mA; VcE = 5 V;*2			770	mV
collector capacitance	Сс	IE = ie = 0; VcB = 10 V; f = 1 MHz		2.5		pF
emitter capacitance	Ce	Ic = ic = 0; VEB = 500 mV; f = 1 MHz		11		pF
transition frequency	fT	Ic = 10 mA; VcE = 5 V; f = 100 MHz	100			MHz
noise figure	F	Ic = 200 μA; Vce = 5 V; Rs = 2 k Ω ,f = 10 Hz to 15.7 kHz			4	dB
Tioise rigule	r	Ic = 200 μA; Vce = 5 V; Rs = 2 k Ω ,f = 1 kHz; B = 200 Hz			4	dB

 $^{^{*}1\ \}text{VBEsat}$ decreases by about 1.7 mV/K with increasing temperature.

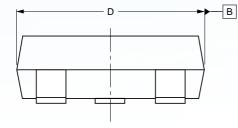
■ hFE Classification

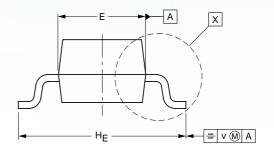
TYPE	EVBC849B-S1	EVBC849C-S1	EVBC850B-S1	EVBC850C-S1
Marking	2B	2C	2F	2G

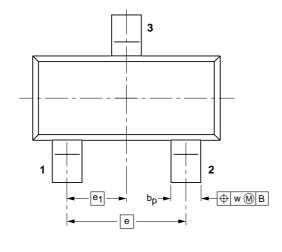
^{*2} VBE decreases by about 2 mV/K with increasing temperature.

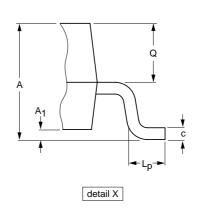


■ SOT-23











DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁ max.	bp	С	D	E	e	e ₁	H _E	Lp	ø	٧	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1



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